

SANYO

No.2124A

DS462

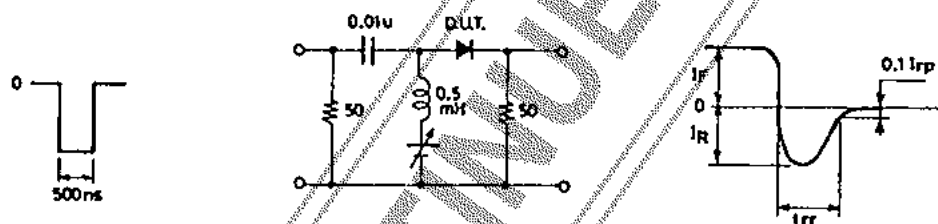
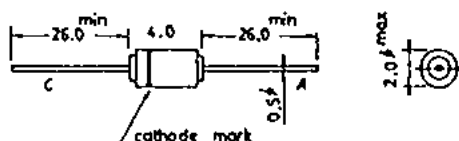
Silicon Epitaxial Planar Type

High-Voltage Switching Diode**Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$**

Peak Reverse Voltage	V_{RM}	-250	V
Reverse Voltage	V_R	-200	V
Peak Forward Current	I_{FM}	600	mA
Average Rectified Current	I_O	200	mA
Surge Forward Current	I_{FSM}	2000	mA
Allowable Power Dissipation	P	400	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +175	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Forward Voltage	V_{F1}	$I_F = 1\text{mA}$			0.8	V
	V_{F2}	$I_F = 100\text{mA}$		0.95	1.2	V
Reverse Current	I_R	$V_R = -200\text{V}$			-0.5	μA
Interterminal Capacitance	c	$V_R = 0\text{V}, f = 1\text{MHz}$		1.0		pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 10\text{mA}, R_L = 50\Omega$			60	ns

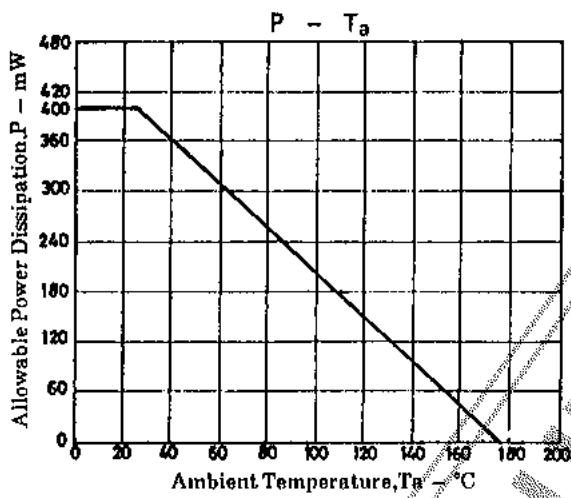
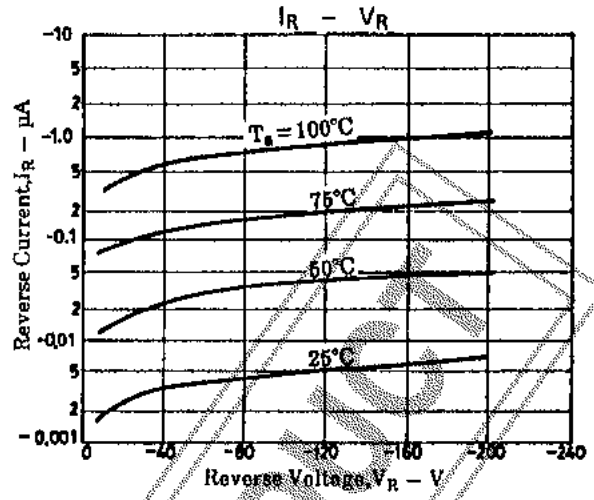
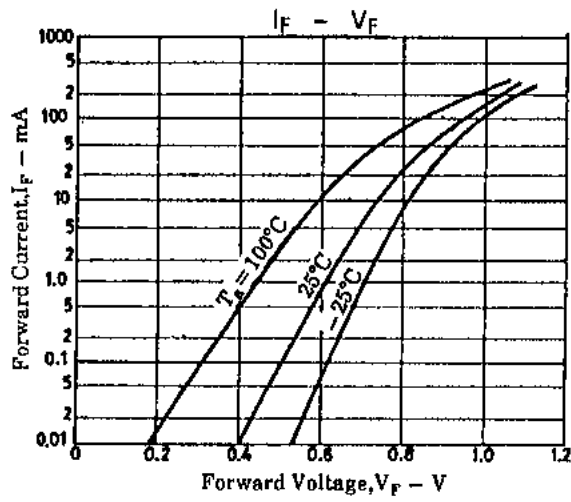
Reverse Recovery Time Test Circuit**Case Outline 1080**
(unit: mm)C: Cathode
A: Anode

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Specifications and information herein are subject to change without notice.

SANYO Electric Co., Ltd. Semiconductor Overseas Marketing Div.
 Natsume Bldg., 18-6, 2-chome, Yushima, Bunkyo-ku, TOKYO 113 JAPAN

2239TA, TS No.2124-1/2



DISCONTINUED PRODUCT